

# **Excellent Integrated System Limited**

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

ON Semiconductor NSVT489AMT1G

For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



**Distributor of ON Semiconductor: Excellent Integrated System Limited** Datasheet of NSVT489AMT1G - TRANS NPN 30V 2A TSOP-6 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

## NST489AMT1, NSVT489AMT1G

## High Current Surface Mount NPN Silicon Low V<sub>CE(sat)</sub> Switching Transistor for Load Management in Portable Applications

#### Features

- AEC-Q101 Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- Pb–Free Packages are Available\*

#### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current – Continuous	۱ <sub>C</sub>	2.0	А
Collector Current – Peak	I <sub>CM</sub>	3.0	А

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P <sub>D</sub> (Note 1)	535 4.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	234	°C/W
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P <sub>D</sub> (Note 2)	1.180 9.4	W mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	106	°C/W
Thermal Resistance, Junction-to-Lead #1	R <sub>θJL</sub> (Note 1) R <sub>θJL</sub> (Note 2)	110 50	°C/W °C/W
Total Device Dissipation (Single Pulse < 10 s)	P <sub>Dsingle</sub> (Notes 2 and 3)	1.75	W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 with 1 oz and 3.9 mm<sup>2</sup> of copper area.

3. Refer to Figure 8.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



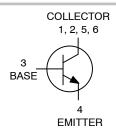
### **ON Semiconductor®**

http://onsemi.com

## 30 VOLTS, 3.0 AMPS NPN TRANSISTOR



TSOP-6 CASE 318G STYLE 6



#### **DEVICE MARKING**



N2 = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NST489AMT1	TSSOP-6	3,000 / Tape & Reel
NST489AMT1G	TSSOP-6 (Pb-Free)	3,000 / Tape & Reel
NSVT489AMT1G	TSSOP-6 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>2.</sup> FR-4 with 1 oz and 645 mm<sup>2</sup> of copper area.

M = Date Code\*



800

700

600

500

300

200

100 0

분400

+125°C

+25°C

-55°C

0.001

0.01

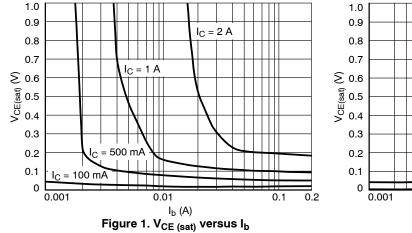
I<sub>c</sub> (A)

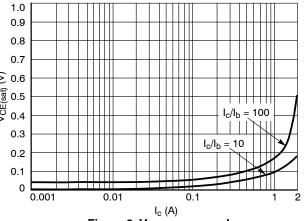
## NST489AMT1, NSVT489AMT1G

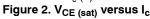
#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

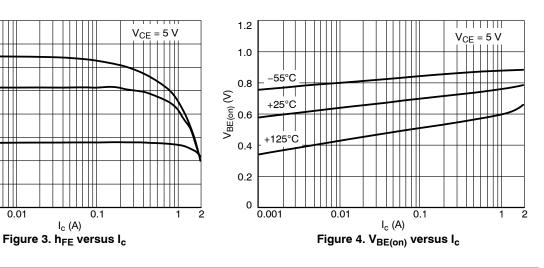
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					•	
Collector – Emitter Breakdown Voltage ( $I_C$ = 10 mA	v, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	30	-	-	V
Collector-Base Breakdown Voltage ( $I_c = 0.1 \text{ mA}, I_E = 0$ )		V <sub>(BR)CBO</sub>	50	-	-	V
Emitter – Base Breakdown Voltage ( $I_E = 0.1 \text{ mA}, I_C$	; = 0)	V <sub>(BR)EBO</sub>	5.0	-	-	V
Collector Cutoff Current (V <sub>CB</sub> = 30 V, $I_E$ = 0)		I <sub>CBO</sub>	-	-	0.1	μA
Collector-Emitter Cutoff Current (V <sub>CES</sub> = 30 V)		ICES	-	-	0.1	μA
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 V)		I <sub>EBO</sub>	-	-	0.1	μA
ON CHARACTERISTICS					•	
DC Current Gain (Note 4)		h <sub>FE</sub>	300 300 200	_ 500 _	_ 900 _	
Collector - Emitter Saturation Voltage (Note 4)	$(I_{C} = 1.0 \text{ A}, I_{B} = 100 \text{ mA})$ $(I_{C} = 0.5 \text{ A}, I_{B} = 50 \text{ mA})$ $(I_{C} = 0.1 \text{ A}, I_{B} = 1.0 \text{ mA})$	V <sub>CE(sat)</sub>	- - -	0.10 0.06 0.05	0.200 0.125 0.075	V
Base – Emitter Saturation Voltage (Note 4) ( $I_C = 1$ .	0 A, I <sub>B</sub> = 0.1 A)	V <sub>BE(sat)</sub>	-	-	1.1	V
Base – Emitter Turn–on Voltage (Note 4) ( $I_C = 1.0$	A, V <sub>CE</sub> = 2.0 V)	V <sub>BE(on)</sub>	-	-	1.1	V
Cutoff Frequency (I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 5.0 V, f = 10	00 MHz	f <sub>T</sub>	200	300	-	MHz
Output Capacitance (f = 1.0 MHz)		C <sub>obo</sub>	-	-	15	pF

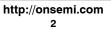
4. Pulsed Condition: Pulse Width  $\leq$  300 µsec, Duty Cycle  $\leq$  2%.





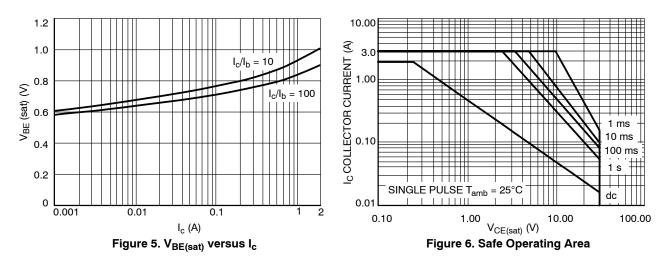








## NST489AMT1, NSVT489AMT1G



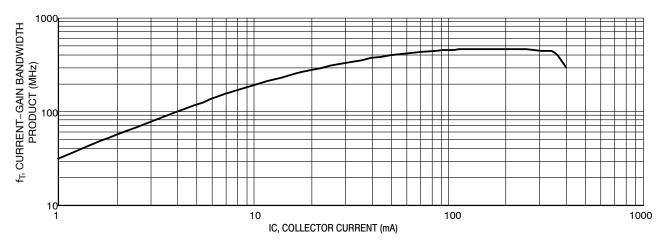
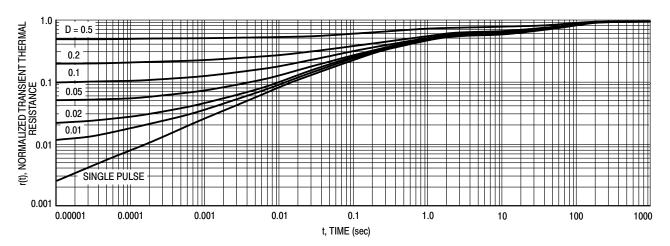


Figure 7. f<sub>T</sub> (MHZ) versus I<sub>C</sub> (mA) V<sub>CE</sub> = 5.0 V

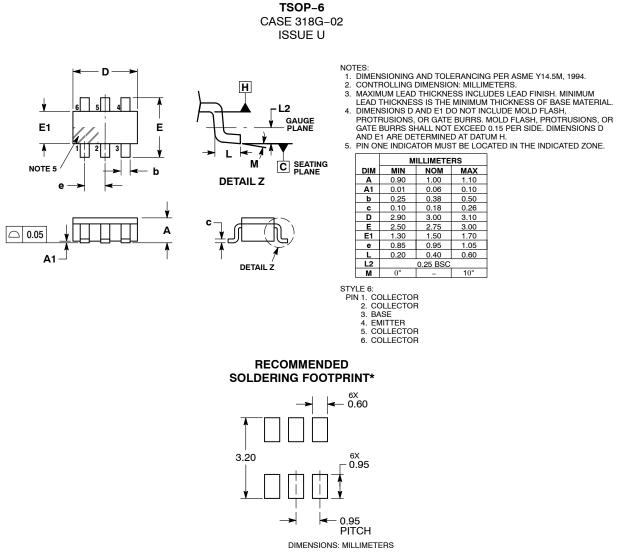






### NST489AMT1, NSVT489AMT1G

#### PACKAGE DIMENSIONS



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 
are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer applications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer applications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer applications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer applications can and do vary in different applications and actual performance may vary over time. All application of the sights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

NST489AMT1/D